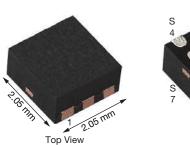


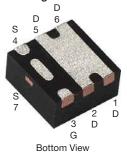
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Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET

PowerPAK® SC-70-6L Single





Marking Code: QBXXXX

PRODUCT SUMMARY				
V _{DS} (V)	-20			
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$	0.125			
$R_{DS(on)}$ (Ω) at $V_{GS} = -2.5 \text{ V}$	0.205			
I _D (A)	-3.75			
Configuration	Single			
Package	PowerPAK SC-70			

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified ^d
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







G O	s •
P-Channel MOSFET	

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-20		
Gate-source voltage		V _{GS}	± 12	V	
Continuous drain current	T _C = 25 °C	l _D	-3.75		
	T _C = 125 °C		-3.75		
Continuous source current (diode conduction) a		I _S	3.75	Α	
Pulsed drain current ^b		I _{DM}	-12		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-8		
Single pulse avalanche energy	L = U.1 MH	E _{AS}	3.2	mJ	
Maximum power dissipation ^b	T _C = 25 °C	D	13.6	w	
	T _C = 125 °C	P_{D}	4.5		
Operating junction and storage temperatu	re range	T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount c	R _{thJA}	90	°C/W	
Junction-to-case (drain)		R_{thJF}	11	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	vise noted) TEST CONDITIONS		TYP.	MAX.	UNIT
Static	OTWIDOL	120	TOONDITIONS	MIN.	1	WAX.	Oitii
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-20	Ι _	<u> </u>	
Gate-source threshold voltage	V _{GS(th)}	ac	V _{GS} = 0, I _D = -250 μA V _{DS} = V _{GS} , I _D = -250 μA		-1.0	-1.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = V_{GS}, I_D = -230 \mu\text{A}$ $V_{DS} = 0 \text{V}, V_{GS} = \pm 12 \text{V}$		-0.6	-	± 100	nA
Zero gate voltage drain current	1G55	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$ $V_{GS} = 0 \text{ V} \qquad V_{DS} = -20 \text{ V}$			_	-1	11/5
	lana	4.4	$V_{DS} = -20 \text{ V}$ $V_{DS} = -20 \text{ V}, T_{J} = 125 \text{ °C}$		_	-50	μΑ
	I _{DSS}	$V_{GS} = 0 \text{ V}$ $V_{GS} = 0 \text{ V}$	$V_{DS} = -20 \text{ V}, T_J = 125 \text{ °C}$ $V_{DS} = -20 \text{ V}, T_J = 175 \text{ °C}$			-150	
On-state drain current ^a	I _{D(on)}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = 20 \text{ V}, 15 = 173 \text{ O}$ $V_{DS} \ge 5 \text{ V}$	-8	_	-	Α
Drain-source on-state resistance a	'D(on)	$V_{GS} = -4.5 \text{ V}$		-0	0.085	0.125	Ω
			I _D = -2.4 A, T _J = 125 °C		-	0.125	
	R _{DS(on)}	0.0	$I_D = -2.4 \text{ A}, T_J = 175 \text{ °C}$		_	0.200	
		$V_{GS} = -2.5 \text{ V}$			0.160	0.205	
Forward transconductance b		$V_{DS} = -10 \text{ V}, I_D = -2.4 \text{ A}$			6	-	S
Dynamic b	915	- 55	10 1,10 21171				
Input capacitance	C _{iss}		S = 0 V V _{DS} = -10 V, f = 1 MHz	_	265	330	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	75	94	
Reverse transfer capacitance	C _{rss}	- 143		_	50	63	
Total gate charge c	Q _q			-	3.4	5.5	
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -2.4 \text{ A}$	-	0.6	-	nC
Gate-drain charge c	Q _{qd}			-	1.1	-	
Gate resistance	R _g	f = 1 MHz		4.8	9.6	14.4	Ω
Turn-on delay time ^c	t _{d(on)}			-	20	30	
Rise time ^c	t _r	V _{DD} =	$V_{DD} = -10 \text{ V, R}_{I} = 5.21 \Omega$		18	27	ns
Turn-off delay time c	t _{d(off)}	$I_D \cong -1.9 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		-	19	28	
Fall time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Char					<u> </u>	<u> </u>	
Pulsed current ^a	I _{SM}			_	_	-12.7	Α
Forward voltage	V _{SD}	I _F = -2 A, V _{GS} = 0			-0.8	-1.2	V

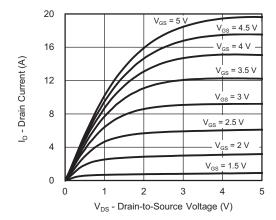
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

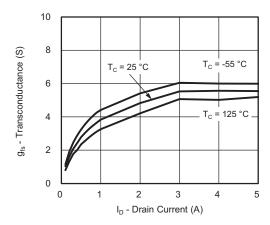
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



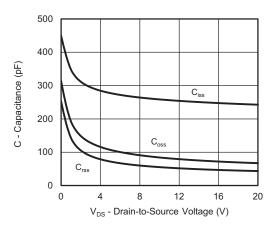
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



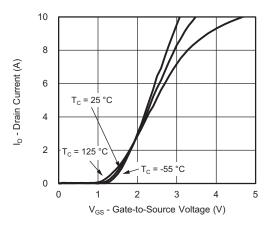
Output Characteristics



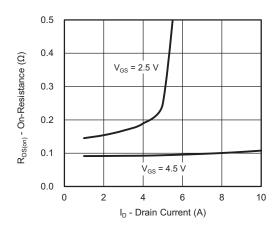
Transconductance



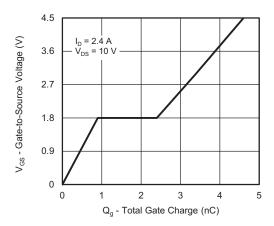
Capacitance



Transfer Characteristics



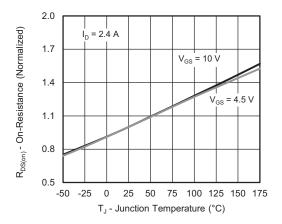
On-Resistance vs. Drain Current



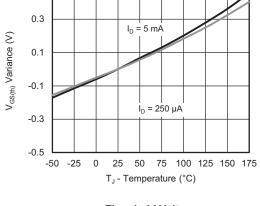
Gate Charge



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

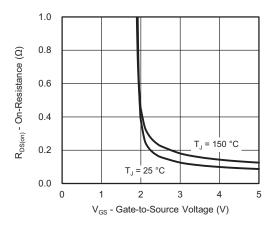


On-Resistance vs. Junction Temperature

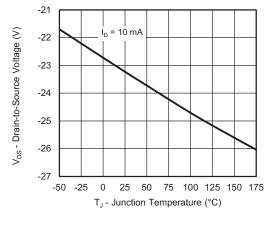


0.5

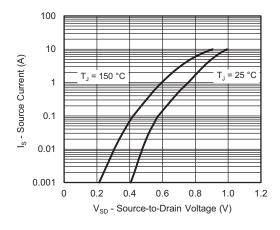
Threshold Voltage



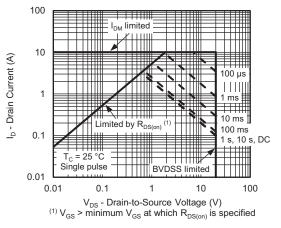
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source-Drain Diode Forward Voltage

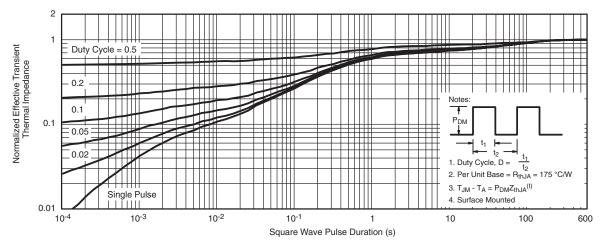


Safe Operating Area

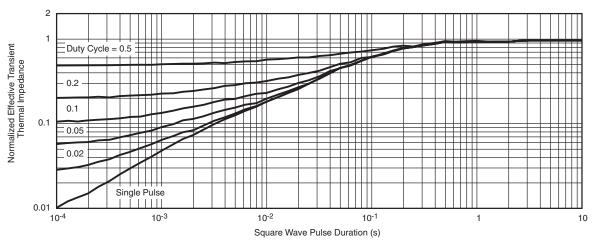
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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